



Docket No.: M4065.0239/P239
(PATENT)

2812
#8/A
Bell
52402

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Larry Hillyer, et al.

Application No.: 09/653,561

Group Art Unit: 2812

Filed: August 31, 2000

Examiner: Ha T. Nguyen

For: METHOD AND MATERIAL FOR
REMOVING ETCH RESIDUE FROM
HIGH ASPECT RATIO CONTACT
SURFACES

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AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated January 17, 2002 (Paper No. 5), rejecting claims 1-44 and 50-53, please amend the above-identified U.S. Patent application as follows. A request for extension of time and appropriate fee are submitted herewith to ensure timeliness of the amendment.

In the Specification:

At page 14, second full paragraph (line 10 to line 20), please replace with the following.

A1
Titanium deposition in the contact opening 20 can be done in a manner known in the art. For example, titanium is deposited on the wafer using a sputter process commonly used with metals. A target containing titanium is surrounded by an argon plasma. Ions from the plasma hit the target surface. The titanium atoms which are